

ADD-A-PAK Generation VII Power Modules Thyristor/Thyristor, 75 A



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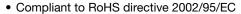
PRODUCT SUMMARY	
I _{T(AV)}	75 A

MECHANICAL DESCRIPTION

The ADD-A-PAK generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- · High voltage
- Industrial standard package
- · Low thermal resistance
- UL approved file E78996



· Designed and qualified for industrial level

RoH:

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- · High surge capability
- Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATING	MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES	UNITS						
I _{T(AV)}	85 °C	75							
I _{T(RMS)}		115	A						
1	50 Hz	1300							
I _{TSM}	60 Hz	1360							
l ² t	50 Hz	8.45	kA ² s						
1-1	60 Hz	7.68	KA-S						
$I^2\sqrt{t}$		84.5	kA²√s						
V _{RRM}	Range	400 to 1600	V						
T _{Stg}		- 40 to 125	°C						
T _J		- 40 (0 125	C						

VSKU71.., VSKV71.. Series

Vishay Semiconductors

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Document Number: 94654

Revision: 17-May-10

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 125 °C mA			
	04	400	500	400				
VSK.71	08	800	900	800	15			
VSK./1	12	1200	1300	1200	15			
	16	1600	1700	1600				

ON-STATE CONDUCTION						
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	I _{T(AV)}	180° conduction	on, half sine wav	re, T _C = 85 °C	75	۸
Marian and a state of the state		DC			115	Α
Maximum continuous RMS on-state current	I _{T(RMS)}	T _C			80	°C
		t = 10 ms	No voltage		1300	
Maximum peak, one-cycle non-repetitive		t = 8.3 ms	reapplied	Sinusoidal	1360	۸
on-state current	I _{TSM}	t = 10 ms	100 % V _{RRM}	half wave, initial $T_J = T_J$ maximum	1093	A
		t = 8.3 ms	reapplied		1140	
		t = 10 ms	No voltage	Later T. and to a	8.45	kA ² s
Manian and 124 for five in a	I ² t	t = 8.3 ms	reapplied		7.68	
Maximum I ² t for fusing	1-1	t = 10 ms	100 % V _{RRM}	Initial $T_J = T_J$ maximum	5.97	
		t = 8.3 ms	reapplied		5.45	
Maximum I²√t for fusing	I ² √t (1)	t = 0.1 ms to 10 ms, no voltage reapplied T _J = T _J maximum			84.5	kA²√s
	. (2)	Low level (3)			0.96	
Maximum value of threshold voltage	V _{T(TO)} (2)	High level (4)	$T_J = T_J \text{ maxin}$	num	1.08	V
Maximum value of on-state	(2)	Low level (3)			3.28	0
slope resistance	r _t ⁽²⁾	High level (4)	T _J = T _J maximum		2.86	mΩ
Maximum on-state voltage drop	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$	T _J = 25 °C		1.72	V
Maximum non-repetitive rate of rise of turned on current	dI/dt	$T_J = 25$ °C, from 0.67 V_{DRM} , $I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500$ mA, $t_r < 0.5$ μ s, $t_p > 6$ μ s			150	A/µs
Maximum holding current	I _H	T _J = 25 °C, anode supply = 6 V, resistive load, gate open circuit		250	mA	
Maximum latching current	ΙL	$T_J = 25$ °C, and	ode supply = 6 \	/, resistive load	400	

Notes

⁽¹⁾ I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$

⁽²⁾ Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$ (3) 16.7 % $\times \pi \times I_{AV} < I < \pi \times I_{AV}$

⁽⁴⁾ $I > \pi \times I_{AV}$



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TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum peak gate power	P _{GM}			12	W	
Maximum average gate power	P _{G(AV)}			3.0	VV	
Maximum peak gate current	I _{GM}			3.0	А	
Maximum peak negative gate voltage	- V _{GM}			10		
		T _J = - 40 °C		4.0	V	
Maximum gate voltage required to trigger	V _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	2.5		
		T _J = 125 °C	resistive load	1.7		
		T _J = - 40 °C		270		
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	150	mA	
		T _J = 125 °C	resistive load	80		
Maximum gate voltage that will not trigger	V_{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V	
Maximum gate current that will not trigger	I _{GD}	T _J = 125 °C, rated V _{DRM} applied		6	mA	

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 125 °C, gate open circuit	15	mA			
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V			
Maximum critical rate of rise of off-state voltage	dV/dt	T_J = 125 °C, linear to 0.67 V_{DRM}	1000	V/µs			

THERMAL AND MECHA	THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Junction operating and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C			
Maximum internal thermal resistance, junction to case per leg		R _{thJC}	DC operation	0.29	2000			
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1	°C/W			
to heatsink Mounting torque ± 10 %			A mounting compound is recommended and the torque should be rechecked after a period of	4	Nm			
Woulding torque ± 10 70	busbar		3 hours to allow for the spread of the compound.	3	Niii			
Approximate weight				75	g			
				2.7	OZ.			
Case style			JEDEC	TO-240AA	compatible			

∆R CONDU	△R CONDUCTION PER JUNCTION										
DEVICES	SINE HALF WAVE CONDUCTION				RECTANGULAR WAVE CONDUCTION				LIMITE		
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.71	0.052	0.062	0.079	0.116	0.197	0.037	0.064	0.085	0.121	0.200	°C/W

Note

• Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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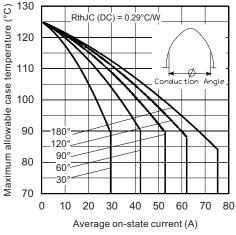


Fig. 1 - Current Ratings Characteristics

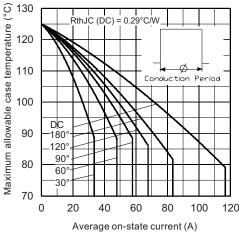


Fig. 2 - Current Ratings Characteristics

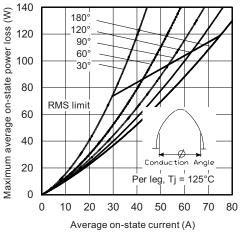


Fig. 3 - On-State Power Loss Characteristics

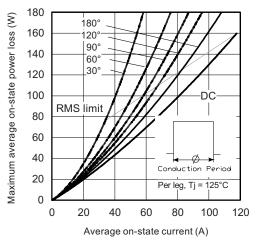


Fig. 4 - On-State Power Loss Characteristics

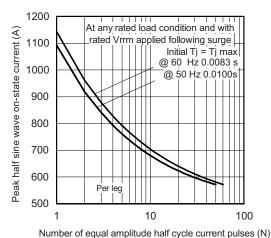


Fig. 5 - Maximum Non-Repetitive Surge Current

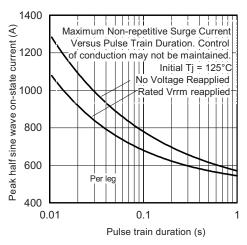


Fig. 6 - Maximum Non-Repetitive Surge Current



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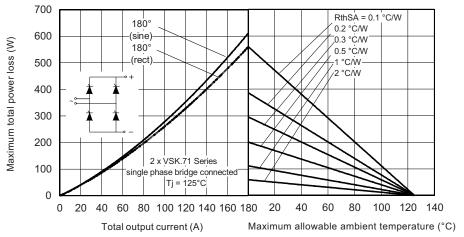


Fig. 7 - On-State Power Loss Characteristics

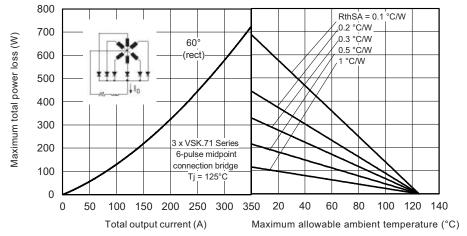


Fig. 8 - On-State Power Loss Characteristics

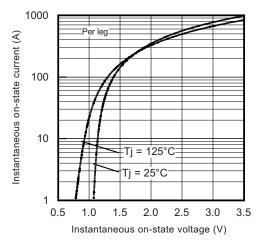


Fig. 9 - On-State Voltage Characteristics

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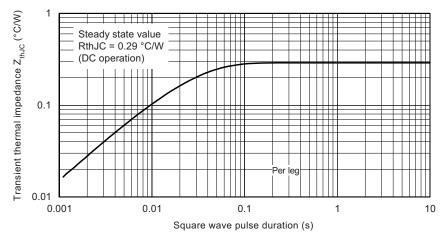
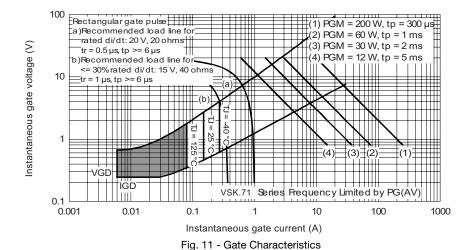
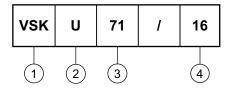


Fig. 10 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code



- 1 Module type
- 2 Circuit configuration (see end of datasheet)
- Current code (75 A)
- Voltage code (see Voltage Ratings table)

Note

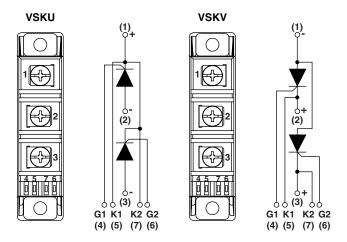
To order the optional hardware go to www.vishay.com/doc?95172





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CIRCUIT CONFIGURATION

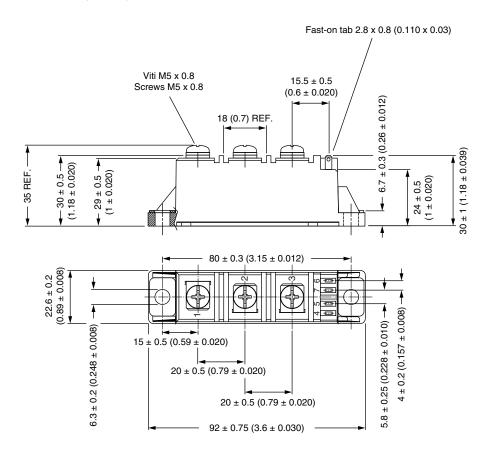


LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95368				



ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)







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